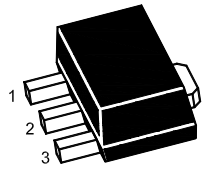
2SB772SQ

Silicon PNP Power Transistor

Features

- High current output up to 3A
- Low saturation voltage
- Complement to 2SD882SQ

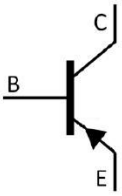


SOT-89

PIN1：Base PIN 2：Collector PIN 3：Emitter

Applications

These devices are intended for use in audio frequency power amplifier and low speed switching applications



Absolute Maximum Ratings (Ta=25℃unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$-V_{CBO}$	40	V
Collector to Emitter Voltage	$-V_{CEO}$	30	V
Emitter to Base Voltage	$-V_{EBO}$	5	V
Collector Current-Continuous	$-I_C$	3	A
Peak Collector Current	$-I_{CP}$	7	A
Base Current - Continuous	$-I_B$	0.6	A
Total Power Dissipation	P_D	1	W
Total Power Dissipation	P_D (Tc=25℃)	10	W
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{STG}	-55～150	℃

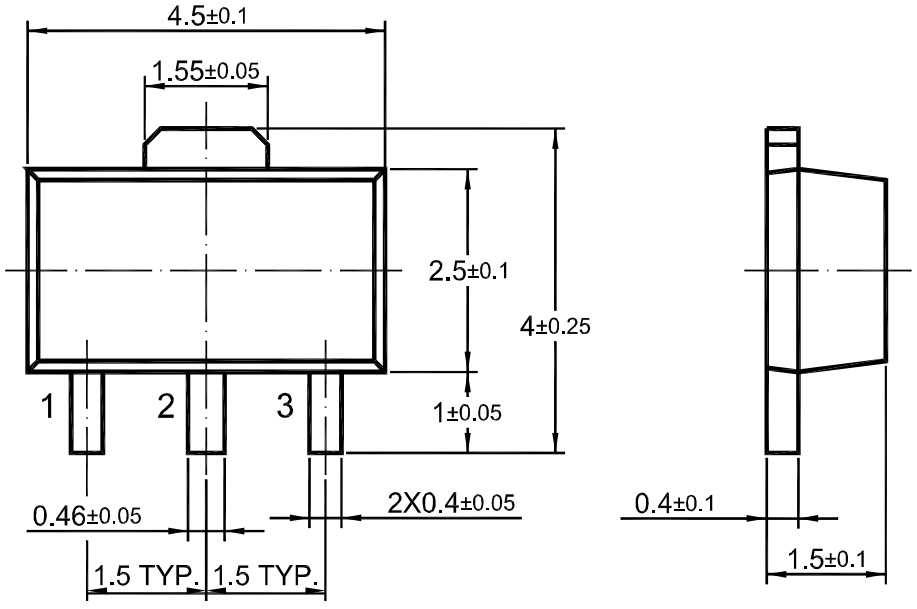
Electrical Characteristics (Ta=25℃ unless otherwise specified)

Parameter		Symbol	Min	Typ	Max	Unit
DC Current Gain						
at $-V_{CE}$ = 2 V, $-I_C$ = 20 mA		h_{FE}	30	-		-
at $-V_{CE}$ = 2 V, $-I_C$ = 1 A Current Gain Group	R	h_{FE}	60	-	120	-
	Q	h_{FE}	100	-	200	-
	P	h_{FE}	160	-	320	-
	E	h_{FE}	200	-	400	-
Collector Base Cutoff Current	at $-V_{CB}$ = 30 V	$-I_{CBO}$	-	-	1	μA
Emitter Base Cutoff Current	at $-V_{EB}$ = 3 V	$-I_{EBO}$	-	-	1	μA
Collector Base Breakdown Voltage	at $-I_C$ = 1 mA	$-V_{(BR)CBO}$	40	-	-	V
Collector Emitter Breakdown Voltage	at $-I_C$ = 1 mA	$-V_{(BR)CEO}$	30	-	-	V
Emitter Base Breakdown Voltage	at $-I_E$ = 1 mA	$-V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage	at $-I_C$ = 2 A, $-I_B$ = 200 mA	$-V_{CE(sat)}$	-	-	0.5	V
Base Emitter Saturation Voltage	at $-I_C$ = 2 A, $-I_B$ = 200 mA	$-V_{BE(sat)}$	-	-	2	V
Current Gain Bandwidth Product	at $-V_{CE}$ = 5 V, $-I_C$ = 100 mA	f_T	-	80	-	MHz
Output Capacitance	at $-V_{CB}$ = 10 V, f = 1 MHz	C_{ob}	-	55	-	pF

Package Outline

SOT-89

Unit : mm



Ordering Information

Device	Package	Shipping
2SB772SQ	SOT-89	1000PCS